# 256K x 16 Bit 3.3 V Asynchronous **Fast Static RAM**

The MCM6343 is a 4,194,304-bit static random access memory organized as 262,144 words of 16 bits. Static design eliminates the need for external clocks or timing strobes.

The MCM6343 is equipped with chip enable  $(\overline{E})$ , write enable  $(\overline{W})$ , and output enable  $(\overline{G})$  pins, allowing for greater system flexibility and eliminating bus contention problems. Separate byte enable controls (LB and UB) allow individual bytes to be written and read.  $\overline{\text{LB}}$  controls the lower bits DQL [7:0], while  $\overline{\text{UB}}$  controls the upper bits DQU [7:0].

The MCM6343 is available in a 400 mil, 44-lead small-outline SOJ package ALESEMICON and a 44-lead TSOP Type II package.

- Single 3.3 V Power Supply
- Fast Access Time: 10/11/12/15 ns ٠
- Equal Address and Chip Enable Access Time ٠
- All Inputs and Outputs are TTL Compatible
- Data Byte Control ٠
- Fully Static Operation •
- Power Operation: 200/195/190/180 mA Maximum, Active AC
- Commercial (0°C to 70°C) and • Industrial Temperature (- 40 to 85°C) Options



\* Address (A) and Data (DQU, DQL) signals are assigned by customer, such that PCB layout is optimized for a given design.

#### REV 8 2/2/99





PIN	I ASSIGN	IMENT
АС	1•	44 🛛 A
АЦ	2	43 🛛 A
АС	3	42 🛛 A
A D	4	41 🛛 🖸
АС	5	40 🛛 UB
ĒŪ	6	39 🛛 LB
DQL [	7	38 🛛 DQU
DQL 🛙	8	37 🛛 DQU
DQL E	9	36 🛛 DQU
DQL [	10	35 🛛 DQU
V <sub>DD</sub> [	11	34 🛛 V <sub>SS</sub>
V <sub>SS</sub> D	12	33 🛛 V <sub>DD</sub>
DQL [	13	32 DQU
DQL [	14	31 DQU
DQL [	15	30 DQU
DQL [	16	29 DQU
Wd	17	28 🛛 NC
A C	18	27 🛛 A
АС		26 🛛 A
A		25 🛛 A
АС	21	24 🛛 A
A q	22	23 🛛 A

PIN NAMES
A [17:0] Address Input   E Chip Enable   W Write Enable   G Output Enable   UB Upper Byte Select   LB Lower Byte Select   DQL [7:0] Data I/O, Low Byte   DQU [7:0] Data I/O, High Byte   VDD + 3.3 V Power Supply   VSS Ground   NC No Connection



For More Information On This Product. Go to: www.freescale.com



#### TRUTH TABLE (X = Don't Care)

Ē	G	W	LB	UB	Mode	V <sub>DD</sub> Current	DQL [7:0]	DQU [7:0]
н	Х	Х	х	Х	Not Selected	I <sub>SB1</sub> , I <sub>SB2</sub>	High–Z	High–Z
L	Н	Н	Х	х	Output Disabled	IDDA	High–Z	High–Z
L	Х	Х	Н	Н	Output Disabled	IDDA	High–Z	High–Z
L	L	Н	L	Н	Low Byte Read	IDDA	D <sub>out</sub>	High–Z
L	L	Н	Н	L	High Byte Read	IDDA	High–Z	D <sub>out</sub>
L	L	Н	L	L	Word Read	I <sub>DDA</sub>	D <sub>out</sub>	D <sub>out</sub>
L	Х	L	L	Н	Low Byte Write	I <sub>DDA</sub>	D <sub>in</sub>	High–Z
L	Х	L	Н	L	High Byte Write	IDDA	High–Z	D <sub>in</sub>
L	Х	L	L	L	Word Write	IDDA	D <sub>in</sub>	D <sub>in</sub>

### ABSOLUTE MAXIMUM RATINGS (See Notes)

Rating		Symbol	Value	Unit		
Supply Voltage		V <sub>DD</sub>	- 0.5 to 4.6	V		
Voltage on Any Pin		/oltage on Any Pin		V <sub>in</sub> – 0.5 to V <sub>DD</sub> + 0.5		V
Output Current per Pin		lout	± 20	mA		
Package Power Dissipation		PD	TBD	W		
Temperature Under Bias	Commercial Industrial	T <sub>bias</sub>	- 10 to 85 - 45 to 90	°C		
Operating Temperature	Commercial Industrial	TA	0 to 70 - 45 to 85	°C		
Storage Temperature		T <sub>stg</sub>	– 55 to 150	°C		

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to these high–impedance circuits.

This CMOS memory circuit has been designed to meet the dc and ac specifications shown in the tables, after thermal equilibrium has been established. The circuit is in a test socket or mounted on a printed circuit board and transverse air flow of at least 500 linear feet per minute is maintained.

NOTES:

1. Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to RECOMMENDED OPER-ATING CONDITIONS. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.

2. All voltages are referenced to  $\mathsf{V}_{\ensuremath{\mathsf{SS}}\xspace}$  .

3. Power dissipation capability will be dependent upon package characteristics and use environment.

### PRODUCT CONFIGURATIONS

			Power S	upply
Part Number	Commercial	Industrial	+ 10%, – 5%	± 10%
MCM6343YJ10B & MCM6343YJ10BR	~		~	
MCM6343YJ11 & MCM6343YJ11R	~			1
MCM6343YJ12 & MCM6343YJ12R	$\sim$			1
MCM6343YJ15 & MCM6343YJ15R	$\sim$			1
MCM6343TS10B & MCM6343TS10BR	$\sim$		~	
MCM6343TS11 & MCM6343TS11R	$\sim$			1
MCM6343TS12 & MCM6343TS12R	$\sim$			1
MCM6343TS15 & MCM6343TS15R	$\sim$			
SCM6343YJ11A & SCM6343YJ11AR				1
SCM6343YJ12A & SCM6343YJ12AR				1
SCM6343YJ15A & SCM6343YJ15AR				1
SCM6343TS11A & SCM6343TS11AR				1
SCM6343TS12A & SCM6343TS12AR				1
SCM6343TS15A & SCM6343TS15AR		1		$\checkmark$



### DC OPERATING CONDITIONS AND CHARACTERISTICS

 $(V_{DD} = 3.3 \text{ V} \pm 0.3 \text{ V}, \text{T}_{A} = 0 \text{ to } 70^{\circ}\text{C}, V_{DD} = 3.3 \text{ V} + 0.3 \text{ V}, -0.15 \text{ V} \text{ for 10 ns Device})$ 

## $(T_A = -40 \text{ to } 85^{\circ}\text{C} \text{ for Industrial Temperature Option})$

### **RECOMMENDED OPERATING CONDITIONS**

Parameter	Symbol	Min	Тур	Max	Unit
Power Supply Voltage	V <sub>DD</sub>	3	3.3	3.6	V
Input High Voltage	VIH	2.2	_	V <sub>DD</sub> + 0.3**	V
Input Low Voltage	VIL	- 0.5*		0.8	V

 $^{*}$  V<sub>IL</sub> (min) = - 0.5 V dc; V<sub>IL</sub> (min) = - 2.0 V ac (pulse width  $\le$  20 ns) for I  $\le$  20.0 mA. \*\* V<sub>IH</sub> (max) = V<sub>DD</sub> + 0.3 V dc; V<sub>IH</sub> (max) = V<sub>DD</sub> + 2.0 V ac (pulse width  $\le$  20 ns) for I  $\le$  20.0 mA.

### DC CHARACTERISTICS

Parameter		Symbol	Min	Max	Unit
Input Leakage Current (All Inputs, $V_{in} = 0$ to $V_{DD}$ )		likg(l)	_	±1	μΑ
Output Leakage Current ( $\overline{E} = V_{IH}, V_{out} = 0$ to $V_{DD}$ )		l <sub>lkg</sub> (O)	—	±1	μΑ
Output Low Voltage	(I <sub>OL</sub> = + 4 mA) (I <sub>OL</sub> = + 100 μA)	VOL	—	0.4 V <sub>SS</sub> + 0.2	V
Output High Voltage	(I <sub>OH</sub> = – 4 mA) (I <sub>OH</sub> = – 100 μA)	VOH	2.4 V <sub>DD</sub> – 0.2	-	V

### **POWER SUPPLY CURRENTS**

Parameter	Symbol	0 to 70°C	– 40 to 85°C	Unit	
AC Active Supply Current (I <sub>out</sub> = 0 mA, V <sub>CC</sub> = Max)	MCM6343–10: t <sub>AVAV</sub> = 10 ns MCM6343–11: t <sub>AVAV</sub> = 11 ns MCM6343–12: t <sub>AVAV</sub> = 12 ns MCM6343–15: t <sub>AVAV</sub> = 15 ns	ICC	200 195 190 180	260 255 250 240	mA
AC Standby Current ( $V_{CC} = Max$ , $\overline{E} = V_{IH}$ , No Other Restrictions on Other Inputs)	MCM6343–10: t <sub>AVAV</sub> = 10 ns MCM6343–11: t <sub>AVAV</sub> = 11 ns MCM6343–12: t <sub>AVAV</sub> = 12 ns MCM6343–15: t <sub>AVAV</sub> = 15 ns	I <sub>SB1</sub>	45 40 35 30	55 55 55 50	mA
CMOS Standby Current ( $\overline{E} \geq V_{CC} - 0.2$ V, $V_{in} \leq (V_{CC} = Max, f = 0$ MHz)	$V_{SS}$ + 0.2 V or $\geq V_{CC}$ – 0.2 V)	I <sub>SB2</sub>	8	10	mA

#### CAPACITANCE (f = 1.0 MHz, dV = 3.0 V, T<sub>A</sub> = 25°C, Periodically Sampled Rather Than 100% Tested)

Parameter	Symbol	Тур	Max	Unit
Address Input Capacitance	C <sub>in</sub>	_	6	pF
Control Input Capacitance	C <sub>in</sub>	_	6	pF
Input/Output Capacitance	C <sub>I/O</sub>	_	8	pF



### AC OPERATING CONDITIONS AND CHARACTERISTICS

 $(V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}, \text{T}_{A} = 0 \text{ to } 70^{\circ}\text{C}, \text{ V}_{DD} = 3.3 \text{ V} + 0.3 \text{ V}, -0.15 \text{ V} \text{ for 10 ns Device} )$   $(\text{T}_{A} = -40 \text{ to } 85^{\circ}\text{C} \text{ for Industrial Temperature Option} )$ 

Logic Input Timing Measurement Reference Level	1.50 V
Logic Input Pulse Levels	0 to 3.0 V
Input Rise/Fall Time	2 ns

Output Timing Reference Level	1.50 V
Output Load See F	igure 1

#### READ CYCLE TIMING (See Notes 1, 2, and 3)

		MCM6	343–10	MCM6	343–11	MCM6	343–12	MCM6	343–15		
Parameter	Symbol	Min	Мах	Min	Max	Min	Max	Min	Max	Unit	Notes
Read Cycle Time	t <sub>AVAV</sub>	10	—	11	—	12	—	15	_	ns	4
Address Access Time	<sup>t</sup> AVQV	_	10	_	11		12		15	ns	
Enable Access Time	<sup>t</sup> ELQV	_	10	_	11		12	<b>R</b> +	15	ns	5
Output Enable Access Time	<sup>t</sup> GLQV	_	4	_	4	—	4	_	5	ns	
Output Hold from Address Change	<sup>t</sup> AXQX	3	_	3	-	3 0	<u> </u>	3	_	ns	
Enable Low to Output Active	<sup>t</sup> ELQX	3	—	3		3	—	3	_	ns	6, 7, 8
Output Enable Low to Output Active	<sup>t</sup> GLQX	0	—	0	-	0	_	0	_	ns	6, 7, 8
Enable High to Output High–Z	<sup>t</sup> EHQZ	0	5	0	6	0	6	0	7	ns	6, 7, 8
Output Enable High to Output High–Z	<sup>t</sup> GHQZ	0	4	0	4	0	4	0	5	ns	6, 7, 8
Byte Enable Access Time	<sup>t</sup> BLQV	-	5	_	6		6	_	7	ns	
Byte Enable Low to Output Active	<sup>t</sup> BLQX	0	—	0	_	0	_	0	—	ns	6, 7, 8
Byte High to Output High-Z	<sup>t</sup> BHQZ	0	5	0	6	0	6	0	7	ns	6, 7, 8

NOTES:

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1.  $\overline{W}$  is high for read cycle.

2. Product sensitivities to noise require proper grounding and decoupling of power supplies as well as minimization or elimination of bus contention conditions during read and write cycles.

3. Device is continuously selected ( $\overline{E} \le V_{IL}$ ,  $\overline{G} \le V_{IL}$ ).

4. All read cycle timings are referenced from the last valid address to the first transitioning address.

5. Addresses valid prior to or coincident with  $\overline{\mathsf{E}}$  going low.

6. At any given voltage and temperature, tEHQZ max < tELQX min, and tGHQZ max < tGLQX min, both for a given device and from device to device.

7. This parameter is sampled and not 100% tested.

8. Transition is measured  $\pm$  200 mV from steady–state voltage.



### TIMING LIMITS

The table of timing values shows either a minimum or a maximum limit for each parameter. Input requirements are specified from the external system point of view. Thus, address setup time is shown as a minimum since the system must supply at least that much time. On the other hand, responses from the memory are specified from the device point of view. Thus, the access time is shown as a maximum since the device never provides data later than that time.

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#### WRITE CYCLE 1 (W Controlled; See Notes 1, 2, and 3)

		MCM6343-10		MCM6343-11		MCM6343-12		MCM6343-15			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Notes
Write Cycle Time	<sup>t</sup> AVAV	10	—	11	—	12	—	15	_	ns	4
Address Setup Time	<sup>t</sup> AVWL	0	—	0	—	0	—	0	_	ns	
Address Valid to End of Write	<sup>t</sup> AVWH	7	—	8	—	8	—	10	_	ns	
Address Valid to End of Write $(\overline{G} High)$	<sup>t</sup> AVWH	8	-	9	_	9	_	10	_	ns	
Write Pulse Width	<sup>t</sup> WLWH <sup>t</sup> WLEH	9	_	10	_	10	_	12	_	ns	
Write Pulse Width ( $\overline{G}$ High)	<sup>t</sup> WLWH <sup>t</sup> WLEH	8	_	9	_	9	_	10	<u>6</u> -	ns	
Data Valid to End of Write	<sup>t</sup> DVWH	5	—	6	—	6	-20	7	—	ns	
Data Hold Time	tWHDX	0	—	0	—	0	SG.	0	_	ns	
Write Low to Data High–Z	tWLQZ	0	5	0	6	0	6	0	7	ns	5, 6, 7
Write High to Output Active	tWHQX	3	—	3		3	_	3	—	ns	5, 6, 7
Write Recovery Time	tWHAX	0	—	0	-	0	_	0	—	ns	

## NOTES:

1. A write occurs during the overlap of  $\overline{E}$  low and  $\overline{W}$  low.

2. Product sensitivities to noise require proper grounding and decoupling of power supplies as well as minimization or elimination of bus contention conditions during read and write cycles.

3. If  $\overline{G}$  goes low coincident with or after  $\overline{W}$  goes low, the output will remain in a high-impedance state.

4. All write cycle timings are referenced from the last valid address to the first transitioning address.

5. This parameter is sampled and not 100% tested.

6. Transition is measured  $\pm$  200 mV from steady–state voltage.

7. At any given voltage and temperature, t<sub>WLQZ</sub> max < t<sub>WHQX</sub> min both for a given device and from device to device.

## WRITE CYCLE 1 (W Controlled; See Notes 1, 2, and 3) **t**AVAV A (ADDRESS) tWHAX <sup>t</sup>AVWH E (CHIP ENABLE) **tWLEH** twLwH W (WRITE ENABLE) <sup>t</sup>AVWL - <sup>t</sup>whdx LB, UB (BYTE ENABLE) <sup>t</sup>DVWH D (DATA IN) DATA VALID twlqz HIGH-Z HIGH-Z Q (DATA OUT) tWHQX



#### WRITE CYCLE 2 (E Controlled; See Notes 1, 2, and 3)

		MCM6343-10		MCM6343-11		MCM6343-12		MCM6343-15			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Notes
Write Cycle Time	<sup>t</sup> AVAV	10	—	11	—	12	_	15	—	ns	4
Address Setup Time	<sup>t</sup> AVEL	0	—	0	—	0	_	0	—	ns	
Address Valid to End of Write	<sup>t</sup> AVEH	9	—	10	_	10	_	12	—	ns	
Address Valid to End of Write (G High)	<sup>t</sup> AVEH	8	_	9	_	9	_	10	_	ns	
Enable to End of Write	<sup>t</sup> ELEH, <sup>t</sup> ELWH	9	_	10	_	10	_	12	_	ns	5, 6
Enable to End of Write ( $\overline{G}$ High)	<sup>t</sup> ELEH, <sup>t</sup> ELWH	8	_	9	_	9	_	10	G-	ns	5, 6
Data Valid to End of Write	<sup>t</sup> DVEH	5	—	6	—	6	-20	7	—	ns	
Data Hold Time	<sup>t</sup> EHDX	0	—	0	—	0	<u>7</u> .	0	—	ns	
Write Recovery Time	<sup>t</sup> EHAX	0	_	0	—	0		0	_	ns	

#### NOTES:

1. A write occurs during the overlap of  $\overline{E}$  low and  $\overline{W}$  low.

2. Product sensitivities to noise require proper grounding and decoupling of power supplies as well as minimization or elimination of bus contention conditions during read and write cycles.

3. If  $\overline{G}$  goes low coincident with or after  $\overline{W}$  goes low, the output will remain in a high–impedance state.

4. All write cycle timing is referenced from the last valid address to the first transitioning address.

5. If  $\overline{E}$  goes low coincident with or after  $\overline{W}$  goes low, the output will remain in a high–impedance condition.

6. If E goes high coincident with or before W goes high, the output will remain in a high-impedance condition.





#### WRITE CYCLE 3 (E Controlled; See Notes 1, 2, and 3)

		MCM6343-10		MCM6343-11		MCM6343-12		MCM6343-15			I
		101010343-10		IVICIVI0343-11				101010343-15			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Notes
Write Cycle Time	<sup>t</sup> AVAV	10	_	11	_	12	—	15	_	ns	4
Address Setup Time	<sup>t</sup> AVBL	0		0	—	0	—	0		ns	
Address Valid to End of Write	<sup>t</sup> AVBH	9	—	10	—	10	—	12	_	ns	
Address Valid to End of Write ( $\overline{G}$ High)	<sup>t</sup> AVBH	8	_	9	_	9	-	10	_	ns	
Byte Pulse Width	<sup>t</sup> BLWH <sup>t</sup> BLEH	9	_	10	_	10	-	12	_	ns	
Byte Pulse Width ( $\overline{G}$ High)	<sup>t</sup> BLWH <sup>t</sup> BLEH	8	_	9	_	9	-	10	6-	ns	
Data Valid to End of Write	<sup>t</sup> DVBH	5	_	6	_	6	<u>_0</u>	7	_	ns	
Data Hold Time	<sup>t</sup> BHDX	0	_	0	_	0	SG.	0	_	ns	

NOTES:

1. A write occurs during the overlap of  $\overline{E}$  low and  $\overline{W}$  low.

2. Product sensitivities to noise require proper grounding and decoupling of power supplies as well as minimization or elimination of bus contention conditions during read and write cycles.

3. If G goes low coincident with or after W goes low, the output will remain in a high-impedance state.

4. All write cycle timings are referenced from the last valid address to the first transitioning address.









TS PACKAGE 44-LEAD TSOP TYPE II



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